BC847 series

45 V, 100 mA NPN general-purpose transistors Rev. 9 — 23 September 2014

Product data sheet

1. **Product profile**

1.1 General description

NPN general-purpose transistors in Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number[1]	Package	Package				
	NXP	JEITA	JEDEC			
BC847	SOT23	-	TO-236AB	BC857		
BC847A				BC857A		
BC847B				BC857B		
BC847C				BC857C		
BC847W	SOT323	SC-70	-	BC857W		
BC847AW				BC857AW		
BC847BW			BC857BW			
BC847CW				BC857CW		
BC847T	SOT416	SC-75	-	BC857T		
BC847AT				BC857AT		
BC847BT				BC857BT		
BC847CT				BC857CT		
BC847AM	SOT883	SC-101	-	BC857AM		
BC847BM				BC857BM		
BC847CM				BC857CM		

^[1] Valid for all available selection groups.

1.2 Features and benefits

- General-purpose transistors
- SMD plastic packages
- Three different gain selections
- AEC-Q101 qualified

1.3 Applications

General-purpose switching and amplification



1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	45	V
Ic	collector current			-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	[1]	110	-	800	
	h _{FE} group A			110	180	220	
	h _{FE} group B			200	290	450	
	h _{FE} group C			420	520	800	

^[1] $T_{amb} = 25$ °C unless otherwise specified

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
SOT23, SOT3	23, SOT416		
1	base		_
2	emitter	3	3
3	collector	1 2 006aaa144	1
SOT883			
1	base		
2	emitter	1 3	3
3	collector	2 Transparent top view	1

3. Ordering information

Table 4. Ordering information

Type number[1]	Package					
Name		Description	Version			
BC847	-	plastic surface-mounted package; 3 leads	SOT23			
BC847A						
BC847B						
BC847C						
BC847W	SC-70	plastic surface-mounted package; 3 leads	SOT323			
BC847AW						
BC847BW						
BC847CW						
BC847T	SC-75	plastic surface-mounted package; 3 leads	SOT416			
BC847AT						
BC847BT						
BC847CT						
BC847AM	SC-101	leadless ultra small plastic package; 3 solder lands;	SOT883			
BC847BM		body $1.0 \times 0.6 \times 0.5$ mm				
BC847CM						

^[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]	Type number	Marking code ^[1]
BC847	1H*	BC847T	1N
BC847A	1E*	BC847AT	1E
BC847B	1F*	BC847BT	1F
BC847C	1G*	BC847CT	1G
BC847W	1H*	BC847AM	D4
BC847AW	1E*	BC847BM	D5
BC847BW	1F*	BC847CM	D6
BC847CW	1G*		

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	45	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u>			
	SOT23			-	250	mW
	SOT323			-	200	mW
	SOT416			-	150	mW
	SOT883		[2]	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]				
	SOT23			-	-	500	K/W
	SOT323			-	-	625	K/W
	SOT416			-	-	833	K/W
	SOT883		[2]	-	-	500	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB with 60 μm copper strip line, standard footprint.

^[2] Device mounted on an FR4 PCB with 60 μm copper strip line, standard footprint.

7. Characteristics

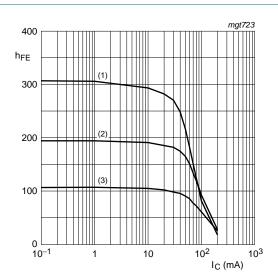
Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$		-	-	15	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \mu\text{A}$					
	h _{FE} group A			-	170	-	
	h _{FE} group B			-	280	-	
	h _{FE} group C			-	420	-	
	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$		110	-	800	
h _{FE} group A			110	180	220		
	h _{FE} group B			200	290	450	
	h _{FE} group C			420	520	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$		-	90	200	mV
		$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[1]	-	200	400	mV
V_{BEsat}	base-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	[2]	-	700	-	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[2]	-	900	-	mV
V_{BE}	base-emitter voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	[2]	580	660	700	mV
		$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$		-	-	770	mV
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	-	1.5	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz		-	11	-	pF
NF	noise figure	$I_{C} = 200 \ \mu A; \ V_{CE} = 5 \ V;$ $R_{S} = 2 \ k\Omega; \ f = 1 \ kHz;$ $B = 200 \ Hz$		-	2	10	dB

^[1] Pulse test: $t_p \leq 300~\mu s;~\delta$ = 0.02.

^[2] V_{BE} decreases by approximately 2 mV/K with increasing temperature.



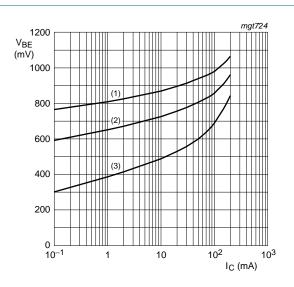
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. Group A: DC current gain as a function of collector current; typical values



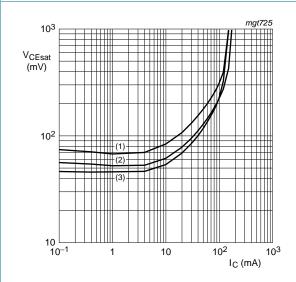
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 2. Group A: Base-emitter voltage as a function of collector current; typical values



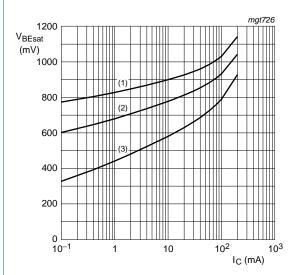
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. Group A: Collector-emitter saturation voltage as a function of collector current; typical values



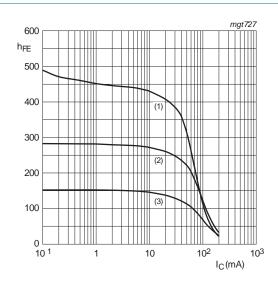
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. Group A: Base-emitter saturation voltage as a function of collector current; typical values



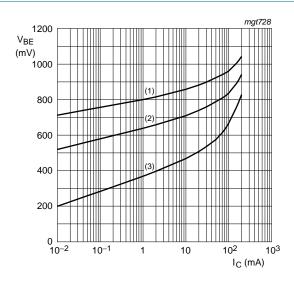
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. Group B: DC current gain as a function of collector current; typical values



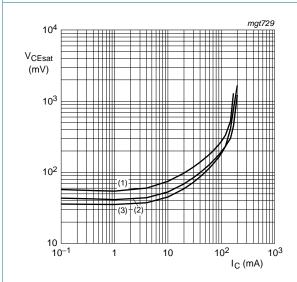
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 6. Group B: Base-emitter voltage as a function of collector current; typical values



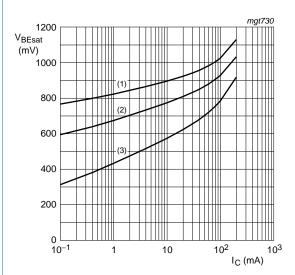
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Group B: Collector-emitter saturation voltage as a function of collector current; typical values



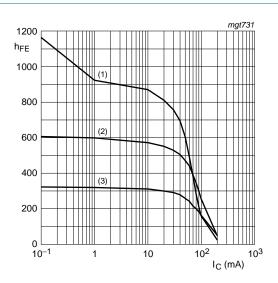
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 8. Group B: Base-emitter saturation voltage as a function of collector current; typical values



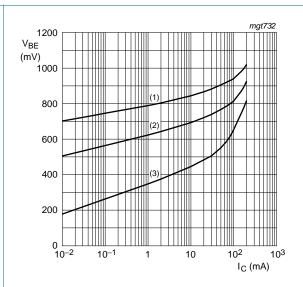
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 9. Group C: DC current gain as a function of collector current; typical values



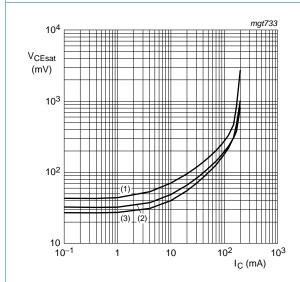
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. Group C: Base-emitter voltage as a function of collector current; typical values



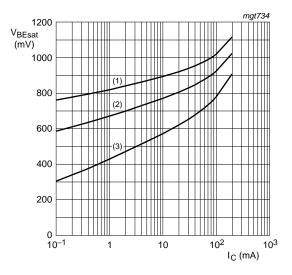
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Group C: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

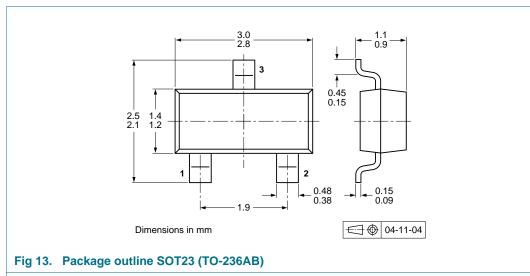
Fig 12. Group C: Base-emitter saturation voltage as a function of collector current; typical values

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



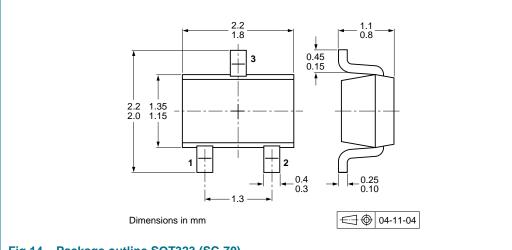
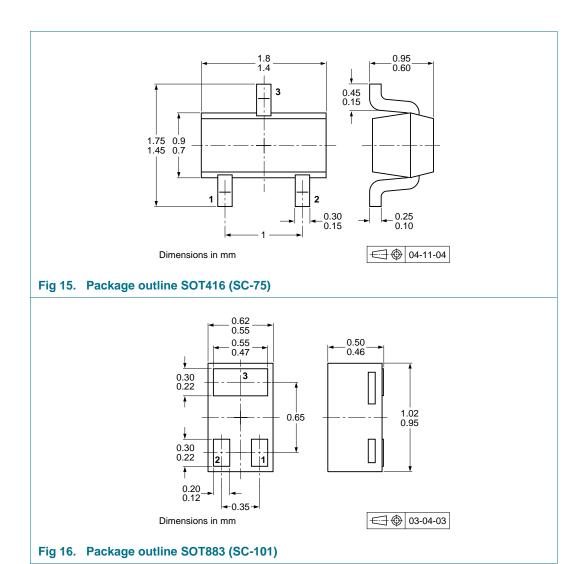
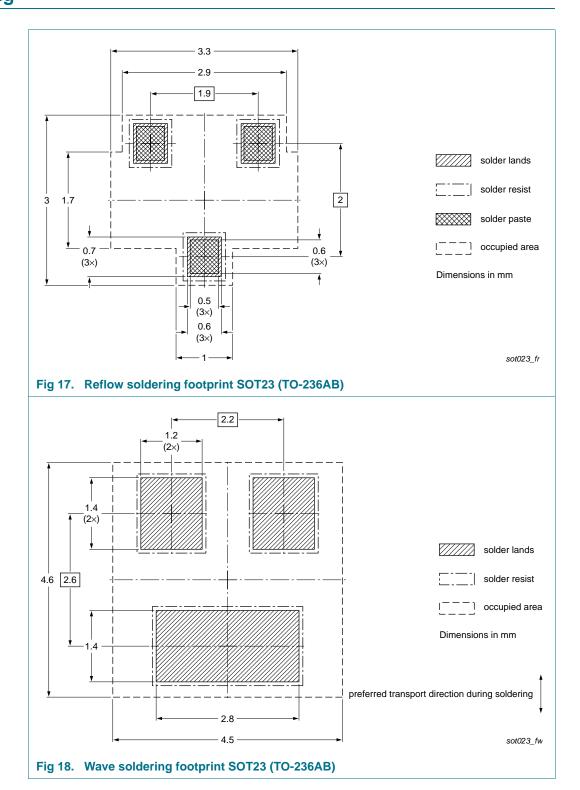
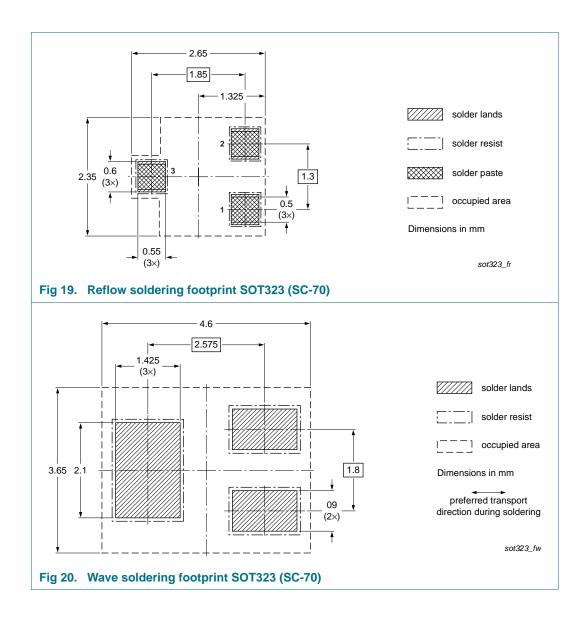


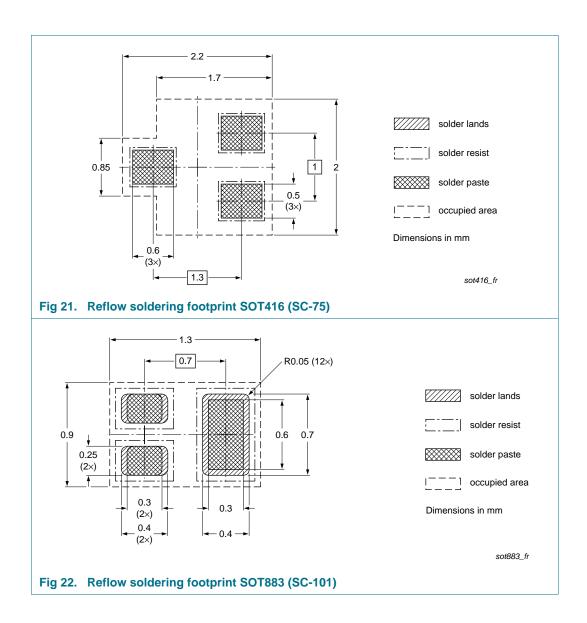
Fig 14. Package outline SOT323 (SC-70)



10. Soldering







11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BC847_SER v.9	20140923	Product data sheet	-	BC847_SER v.8		
Modifications:	Section 1.2	 Section 1.2 "Features and benefits": updated 				
	Section 5 "Limiting values": updated					
	• Figure 5: corrected					
	Section 8 "To	est information": added				
	• <u>Section 12</u> "	Legal information": updated	b			
BC847_SER v.8	20120820	Product data sheet	-	BC847_BC547_SER v.7		
BC847_BC547_SER v.7	20081210	Product data sheet	-	BC847_BC547_SER v.6		
BC847_BC547_SER v.6	20050519	Product data sheet	-	-		

NXP Semiconductors BC847 series

45 V, 100 mA NPN general-purpose transistors

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

BC847_SER

NXP Semiconductors BC847 series

45 V, 100 mA NPN general-purpose transistors

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

BC847 series

NXP Semiconductors

45 V, 100 mA NPN general-purpose transistors

14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data 2
2	Pinning information 2
3	Ordering information 3
4	Marking 3
5	Limiting values4
6	Thermal characteristics
7	Characteristics 5
8	Test information9
8.1	Quality information
9	Package outline 9
10	Soldering
11	Revision history
12	Legal information
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Trademarks16
13	Contact information
14	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by NXP manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B